

SANYO	No.2217A	2SA1450/2SC3708
PNP/NPN Epitaxial Planar Silicon Transistors		
Low-Frequency Driver Applications		

Features

- Adoption of FBET process
- AF amp, AF power amp
- High breakdown voltage $V_{CEO} > 80V$

(): 2SA1450

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector to Base Voltage	V_{CBO}	(-)100	V
Collector to Emitter Voltage	V_{CEO}	(-)80	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)500	mA
Collector Current (Pulse)	I_{CP}	(-)800	mA
Base Current	I_B	(-)100	mA
Collector Dissipation	P_C	600	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

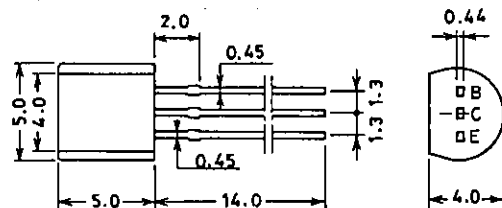
Electrical Characteristics at $T_a = 25^\circ C$

Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)60V, I_E = 0$		(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$		(-)0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-)5V, I_C = (-)50mA$	100*		400*
	$h_{FE(2)}$	$V_{CE} = (-)5V, I_C = (-)400mA$	60		
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)10mA$		120	MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)400mA, I_B = (-)40mA$		0.16	V
				(-0.2) (-0.5)	
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400mA, I_B = (-)40mA$		(-)0.9 (-)1.2	V
Output Capacitance	C_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(7)5	pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)100		V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)80		V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5		V

*: The 2SA1450/2SC3708 are classified by 50mA h_{FE} as follows :

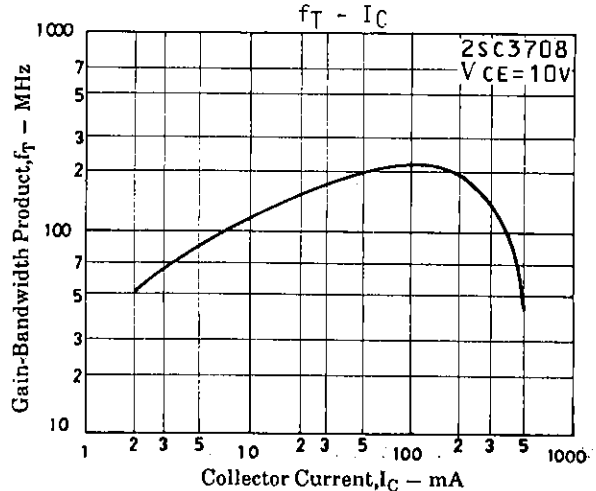
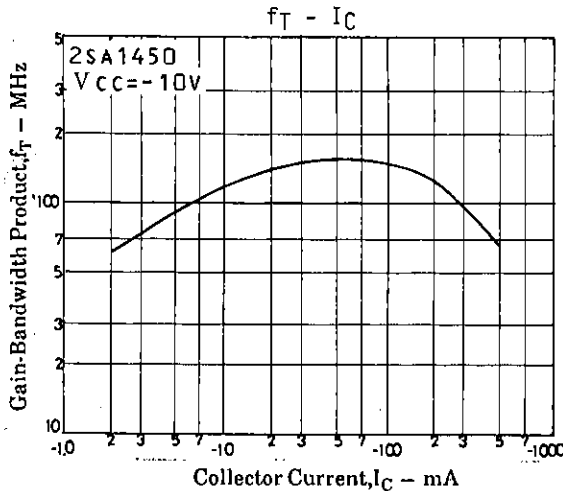
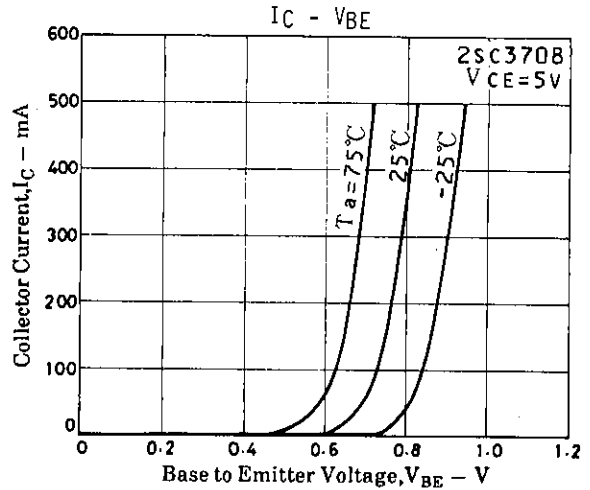
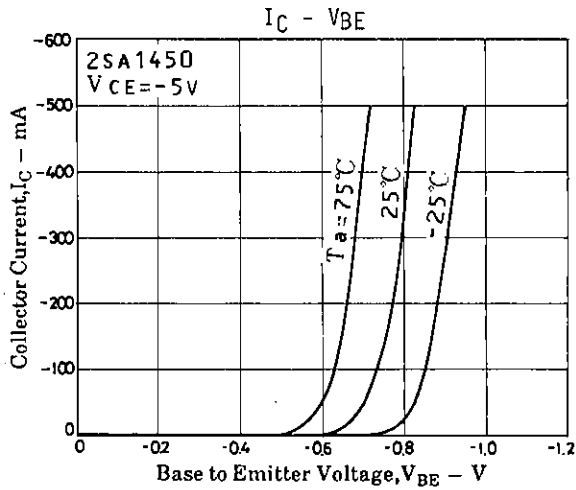
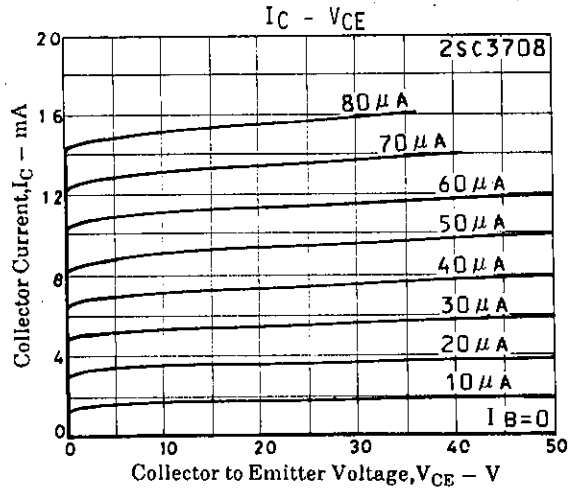
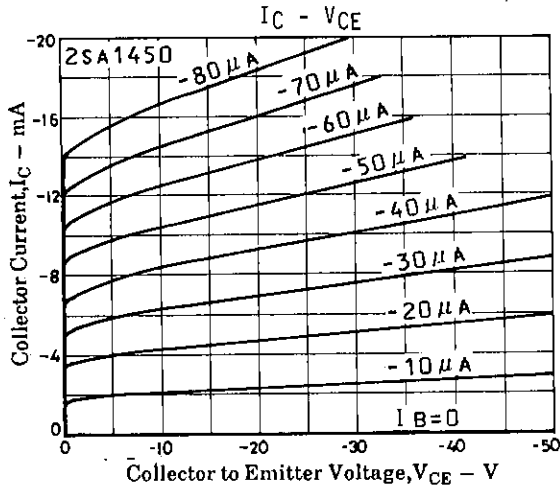
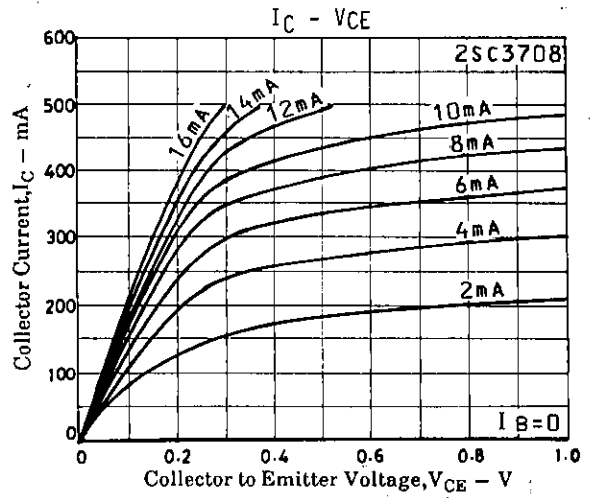
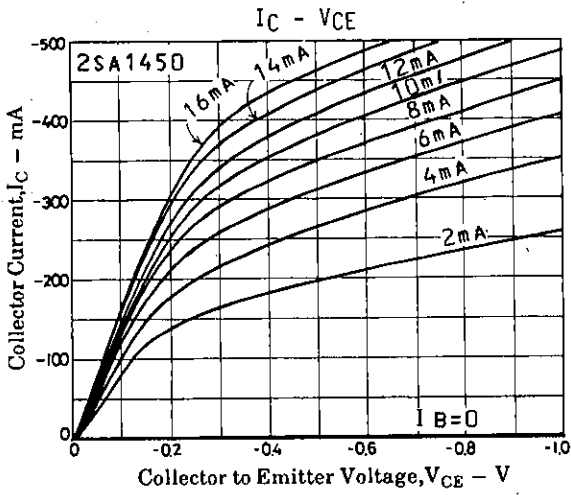
100 R 200	140 S 280	200 T 400
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Package Dimensions 2003A
(unit: mm)

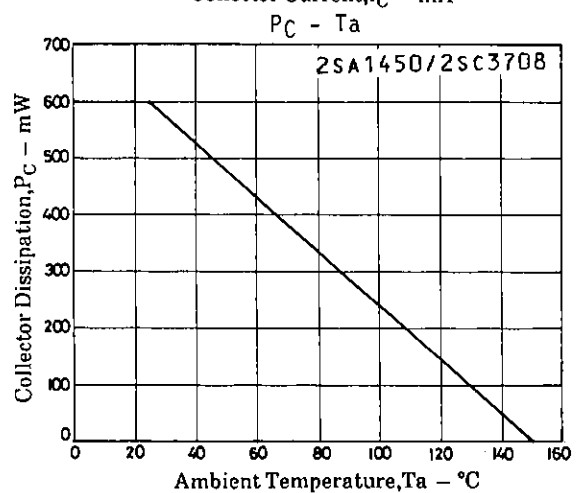
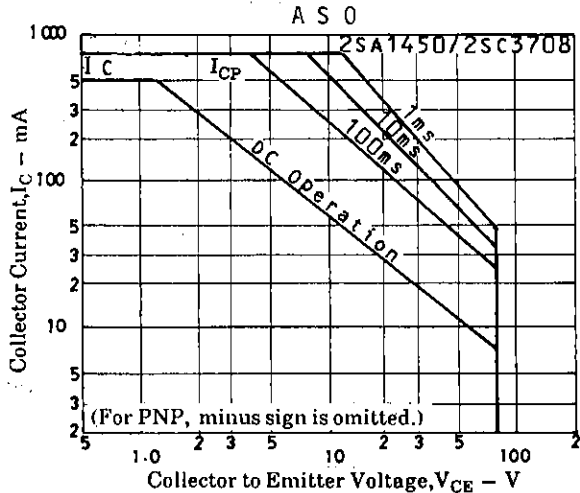
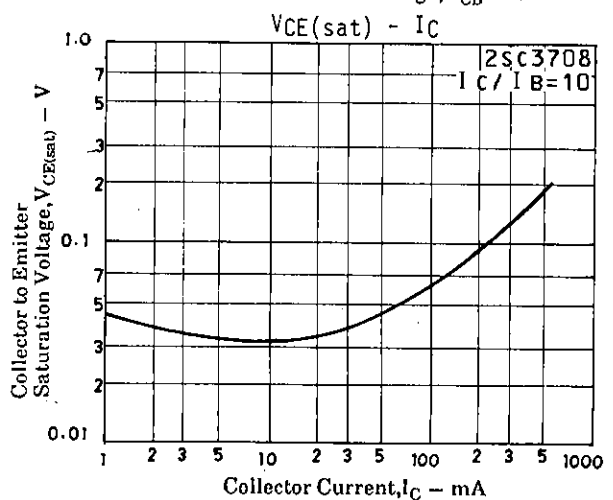
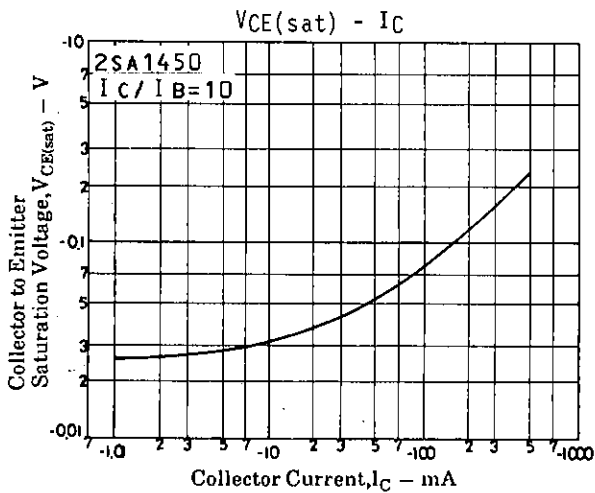
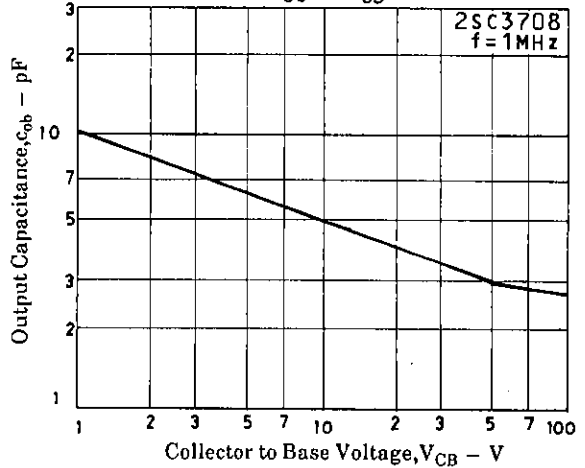
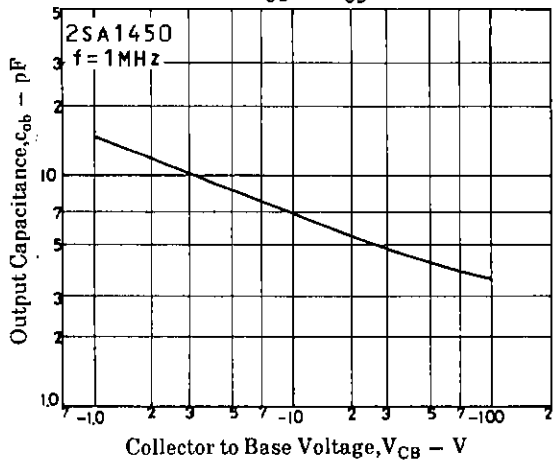
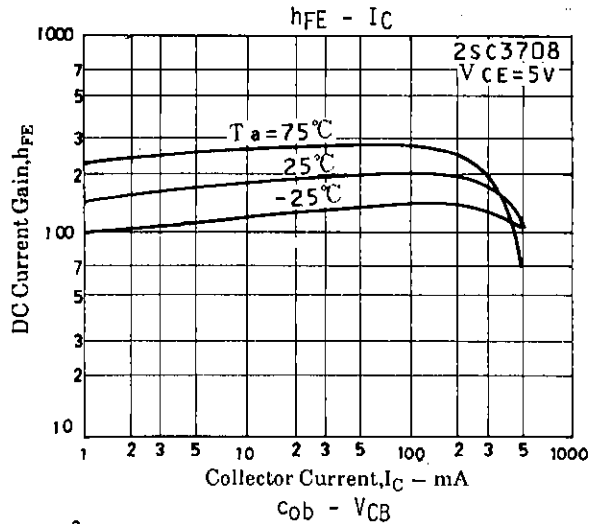
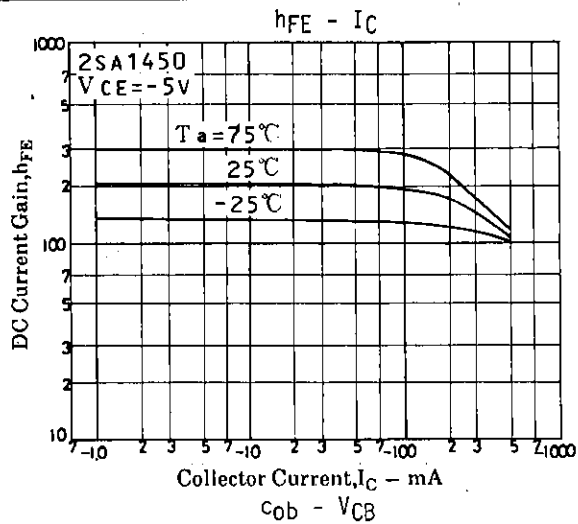


JEDEC: TO-92 B: Base
 EIAJ: SC-43 C: Collector
 SANYO: NP E: Emitter

2SA1450/2SC3708



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